


SANYO Semiconductors

DATA SHEET

P-Channel Silicon MOSFET

FTD1029 — General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 4V drive.
- Mounting height 1.1mm.
- Composite type, facilitating high-density mounting.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-3	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-15	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (1000mm²×0.8mm) 1unit	0.8	W
Total Power Dissipation	P _T	Mounted on a ceramic board (1000mm²×0.8mm)	1.0	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR) _{DSS}	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _D =-30V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _D =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _D =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _D =-10V, I _D =-2A	2.4	4		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-2A, V _{GS} =-10V		56	73	mΩ
	R _{DS(on)2}	I _D =-1A, V _{GS} =-4.5V		100	140	mΩ
	R _{DS(on)3}	I _D =-1A, V _{GS} =-4V		117	164	mΩ
Input Capacitance	C _{iss}	V _D =-10V, f=1MHz		570		pF
Output Capacitance	C _{oss}	V _D =-10V, f=1MHz		100		pF
Reverse Transfer Capacitance	C _{rss}	V _D =-10V, f=1MHz		85		pF

Marking : D1029

Continued on next page.

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SANYO Semiconductor Co., Ltd.

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

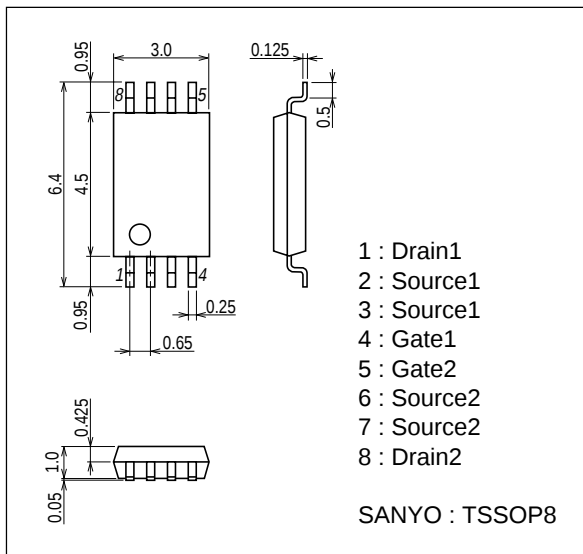
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		11		ns
Rise Time	t_r	See specified Test Circuit.		13		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		49		ns
Fall Time	t_f	See specified Test Circuit.		36		ns
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-10V, I_D=-3A$		11.7		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-3A$		2.04		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-3A$		2.64		nC
Diode Forward Voltage	V_{SD}	$I_S=-3A, V_{GS}=0V$		-0.84	-1.2	V

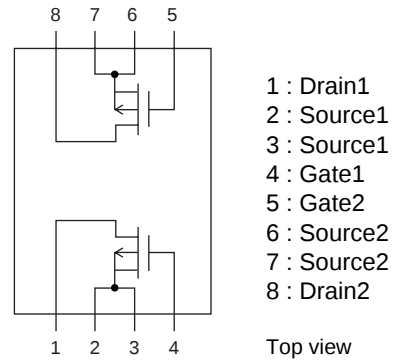
Package Dimensions

unit : mm (typ)

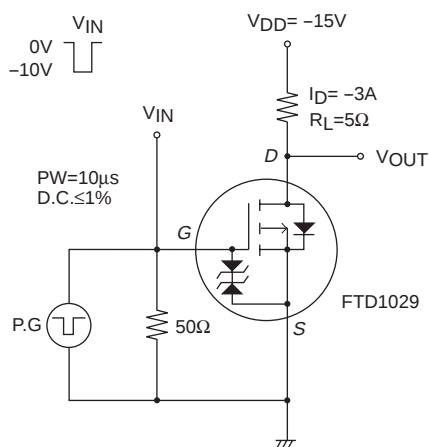
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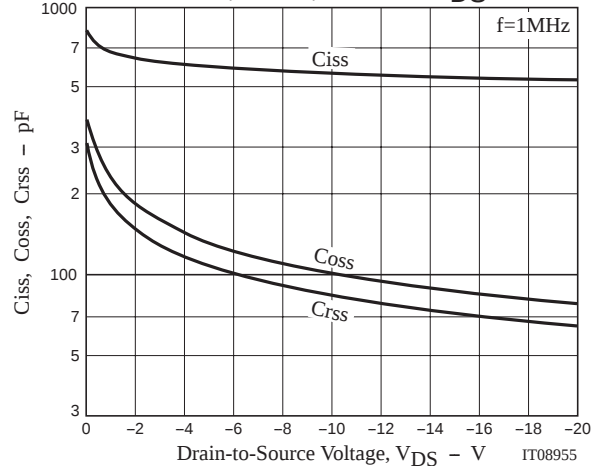
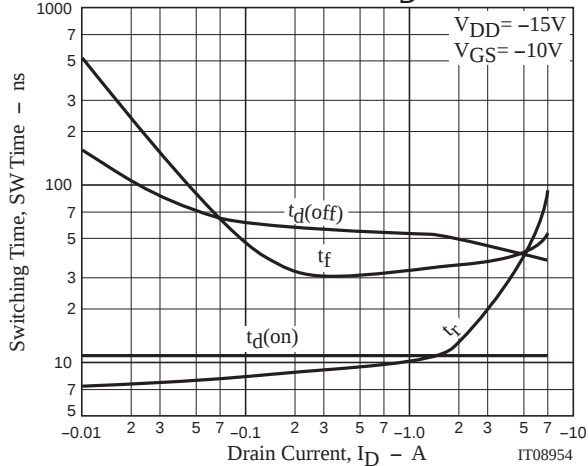
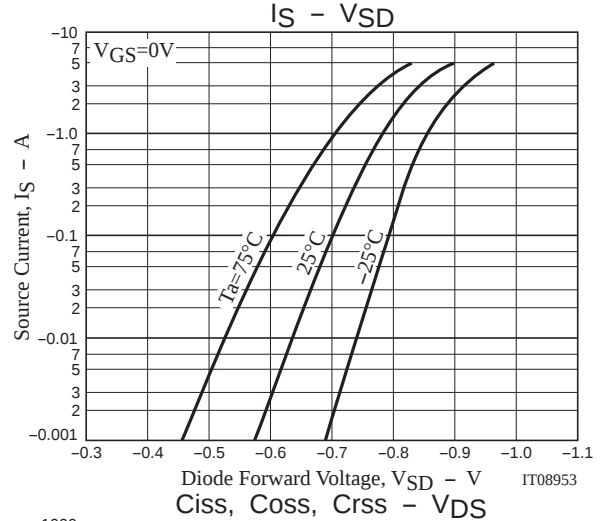
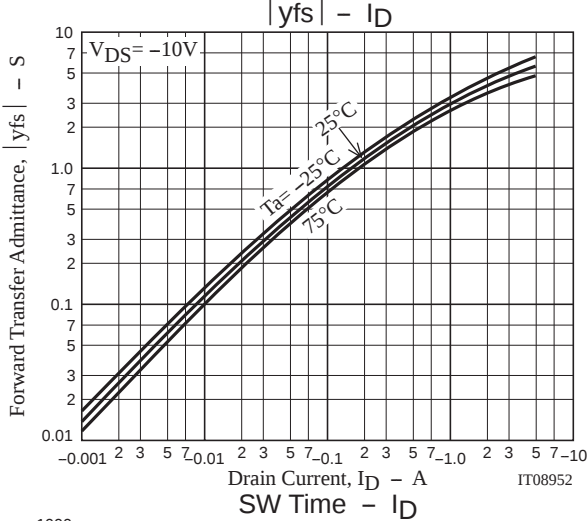
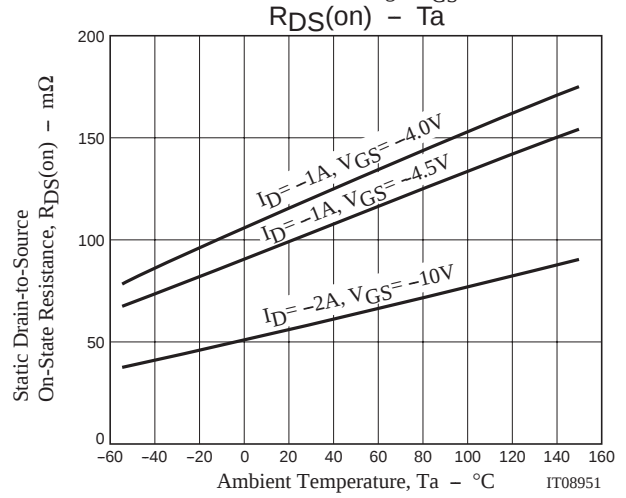
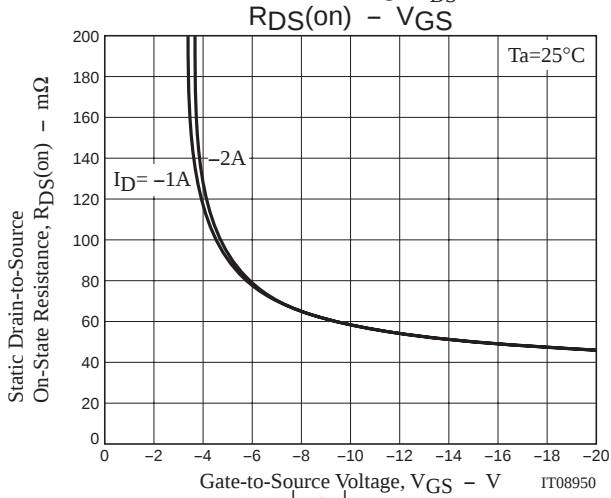
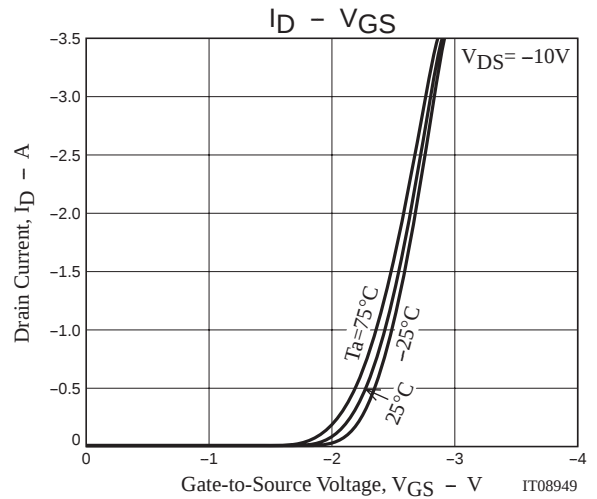
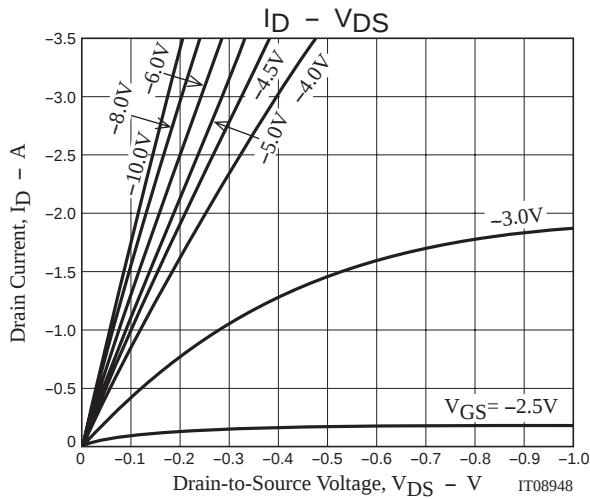


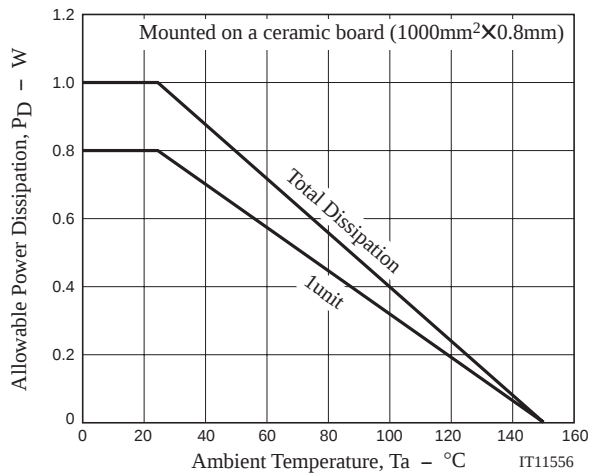
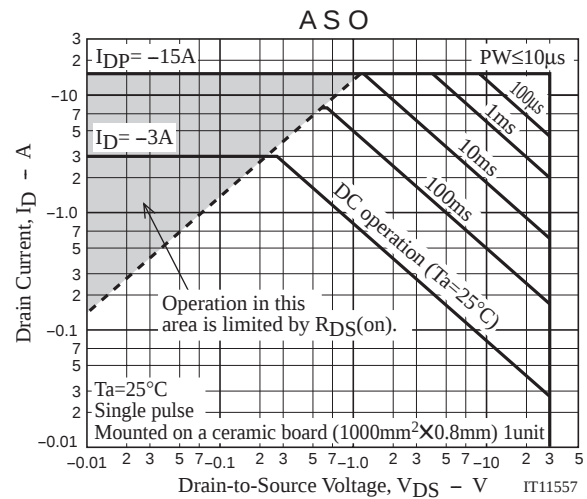
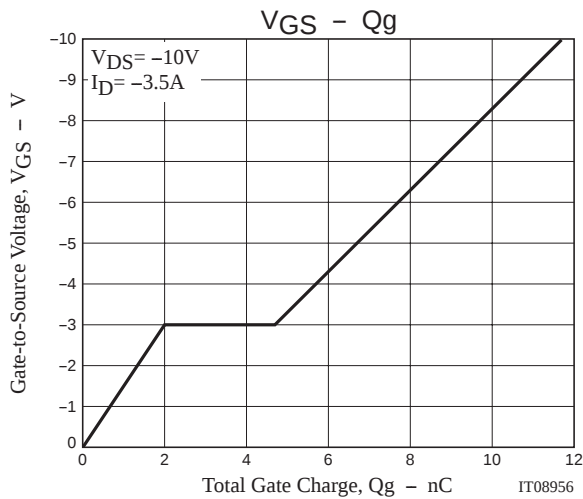
Electrical Connection



Switching Time Test Circuit







Note on usage : Since the FTD1029 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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